



**DMN3730U**

**30V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23**

**Product Summary**

$V_{(BR)DSS}$	Max $R_{DS(on)}$	$I_D$ Max (Note 5) $T_A = 25^\circ C$
30V	460m $\Omega$ @ $V_{GS} = 4.5V$	0.94A
	560m $\Omega$ @ $V_{GS} = 2.5V$	0.85A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

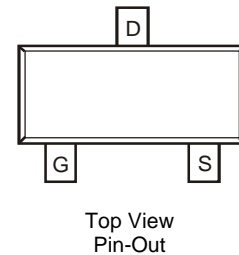
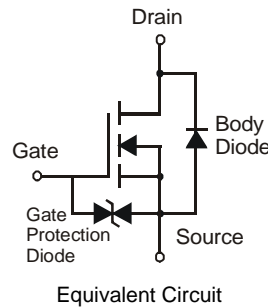
- Load switch
- Portable applications
- Power Management Functions

**Features and Benefits**

- Low  $V_{GS(th)}$ , can be driven directly from a battery
- Low  $R_{DS(on)}$
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin.
- Weight: 0.08 grams (approximate)

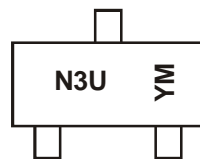


**Ordering Information** (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3730U-7	N3U	7	8	3,000

Notes: 1. No purposefully added lead

**Marking Information**



N3U = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: Y = 2011)  
 M = Month (ex: 9 = September)

Date Code Key

Year Code	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



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**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 8$	V
Continuous Drain Current	Steady State	$T_A = 25^\circ\text{C}$ (Note 5)	$I_D$	0.94	A
		$T_A = 85^\circ\text{C}$ (Note 5)		0.68	
		$T_A = 25^\circ\text{C}$ (Note 4)		0.75	
Pulsed Drain Current (Note 6)			$I_{DM}$	10	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	$P_D$	0.45	W
	(Note 5)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	275	$^\circ\text{C/W}$
	(Note 5)		177	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
2. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
  3. Device mounted on 25mm X 25mm square copper plate with FR-4 substrate PC board, 2oz copper
  4. Device mounted on minimum recommended pad layout test board, 10 $\mu\text{s}$  pulse duty cycle = 1%.



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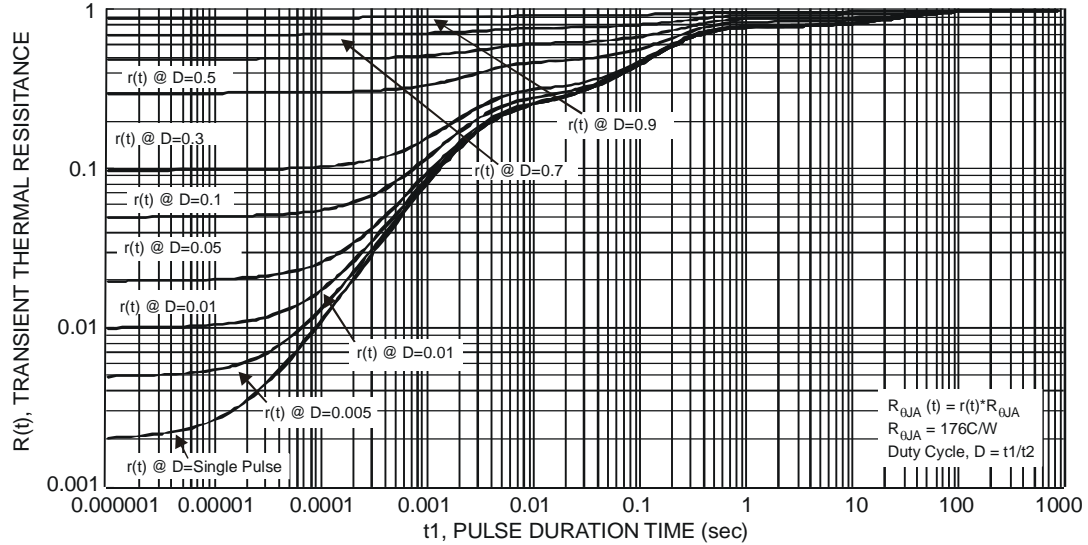


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	3	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45	-	0.95	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>	-	-	460	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
				560		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 100mA
				730		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 75mA
Forward Transfer Admittance	Y <sub>fs</sub>	40	-	-	mS	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 300mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	-	64.3	-	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	6.1	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	4.5	-	pF	
Gate Resistance	R <sub>g</sub>	-	70	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	-	1.6	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 1A
Gate-Source Charge	Q <sub>gs</sub>	-	0.2	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.2	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	3.5	-	ns	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1A V <sub>GS</sub> = 10V, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	-	2.8	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	38	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	13	-	ns	

Notes: 5. Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300μs; duty cycle ≤ 2%  
6. For design aid only, not subject to production testing.